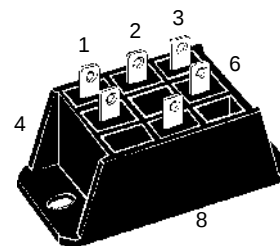
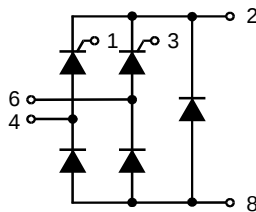


Half Controlled Single Phase Rectifier Bridge with Freewheeling Diode

$$I_{dAVM} = 40 \text{ A}$$

$$V_{RRM} = 800\text{-}1600 \text{ V}$$

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
900	800	VHF 36-08io5
1300	1200	VHF 36-12io5
1500	1400	VHF 36-14io5
1700	1600	VHF 36-16io5



Symbol	Test Conditions		Maximum Ratings	
I_{dAV}	$T_K = 85^{\circ}\text{C}$, module module per leg		36	A
I_{dAVM}			40	A
I_{FRMS}^1 , I_{TRMS}			28	A
I_{FSM}^1 , I_{TSM}	$T_{VJ} = 45^{\circ}\text{C}$;	$t = 10\text{ ms}$ (50 Hz), sine	320	A
	$V_R = 0\text{ V}$	$t = 8.3\text{ ms}$ (60 Hz), sine	350	A
	$T_{VJ} = T_{VJM}$	$t = 10\text{ ms}$ (50 Hz), sine	280	A
	$V_R = 0\text{ V}$	$t = 8.3\text{ ms}$ (60 Hz), sine	310	A
I^2t	$T_{VJ} = 45^{\circ}\text{C}$	$t = 10\text{ ms}$ (50 Hz), sine	500	A ² s
	$V_R = 0\text{ V}$	$t = 8.3\text{ ms}$ (60 Hz), sine	520	A ² s
	$T_{VJ} = T_{VJM}$	$t = 10\text{ ms}$ (50 Hz), sine	390	A ² s
	$V_R = 0\text{ V}$	$t = 8.3\text{ ms}$ (60 Hz), sine	400	A ² s
$(di/dt)_{cr}$	$T_{VJ} = 125^{\circ}\text{C}$	repetitive, $I_T = 50\text{ A}$	150	A/ μs
	$f = 50\text{ Hz}$, $t_p = 200\text{ }\mu\text{s}$			
	$V_D = 2/3\text{ }V_{DRM}$	non repetitive, $I_T = 1/2 \cdot I_{dAV}$	500	A/ μs
	$I_G = 0.3\text{ A}$, $di_G/dt = 0.3\text{ A}/\mu\text{s}$			
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $V_{DR} = 2/3\text{ }V_{DRM}$		1000	V/ μs
	$R_{GK} = \infty$; method 1 (linear voltage rise)			
V_{RGM}			10	V
P_{GM}	$T_{VJ} = T_{VJM}$	$t_p = 30\text{ }\mu\text{s}$	≤ 10	W
	$I_T = I_{TAVM}$	$t_p = 500\text{ }\mu\text{s}$	≤ 5	W
		$t_p = 10\text{ ms}$	≤ 1	W
P_{GAVM}			0.5	W
T_{VJ}			-40...+125	$^{\circ}\text{C}$
T_{VJM}			125	$^{\circ}\text{C}$
T_{stg}			-40...+125	$^{\circ}\text{C}$
V_{ISOL}	50/60 Hz, RMS	$t = 1\text{ min}$	3000	V~
	$I_{ISOL} \leq 1\text{ mA}$	$t = 1\text{ s}$	3600	V~
M_d	Mounting torque	(M5)	2-2.5	Nm
		(10-32 UNF)	18-22	lb.in.
Weight			50	g

Features

- Package with DCB ceramic base plate
- Isolation voltage 3600 V~
- Planar passivated chips
- ¼" fast-on terminals
- UL registered E 72873

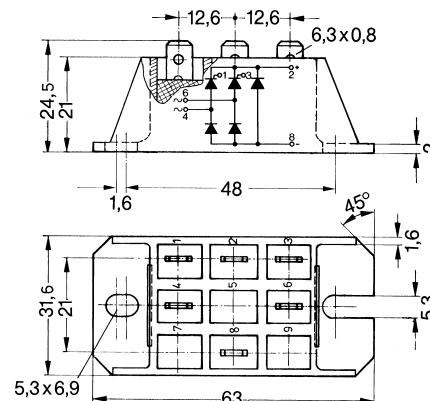
Applications

- Supply for DC power equipment
- DC motor control

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

Dimensions in mm (1 mm = 0.0394")



Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

① for resistive load

IXYS reserves the right to change limits, test conditions and dimensions.

Symbol	Test Conditions	Characteristic Values
I_R, I_D	$V_R = V_{RRM}; V_D = V_{DRM}$ $T_{VJ} = T_{VJM}$ $T_{VJ} = 25^\circ\text{C}$	≤ 5 mA ≤ 0.3 mA
V_T, V_F	$I_T, I_F = 45$ A; $T_{VJ} = 25^\circ\text{C}$	≤ 1.45 V
V_{T0}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)	0.85 V
r_T		13 m Ω
V_{GT}	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	≤ 1.0 V ≤ 1.2 V
I_{GT}	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	≤ 65 mA ≤ 80 mA ≤ 50 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	≤ 0.2 V
I_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	≤ 5 mA
I_L	$I_G = 0.3$ A; $t_G = 30$ μs ; $T_{VJ} = 25^\circ\text{C}$ $di_G/dt = 0.3$ A/ μs ; $T_{VJ} = -40^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	≤ 150 mA ≤ 200 mA ≤ 100 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6$ V; $R_{GK} = \infty$	≤ 100 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.3$ A; $di_G/dt = 0.3$ A/ μs	≤ 2 μs
t_q	$T_{VJ} = 125^\circ\text{C}; I_T = 15$ A; $t_p = 300$ μs ; $V_R = 100$ V	typ. 150 μs
Q_r	$di/dt = -10$ A/ μs ; $dv/dt = 20$ V/ μs ; $V_D = 2/3 V_{DRM}$	75 μC
R_{thJC}	per thyristor (diode); DC current	1.15 K/W
	per module	0.29 K/W
R_{thJK}	per thyristor (diode); DC current	1.55 K/W
	per module	0.39 K/W
d_s	Creeping distance on surface	12.6 mm
d_A	Creepage distance in air	6.3 mm
a	Max. allowable acceleration	50 m/s ²

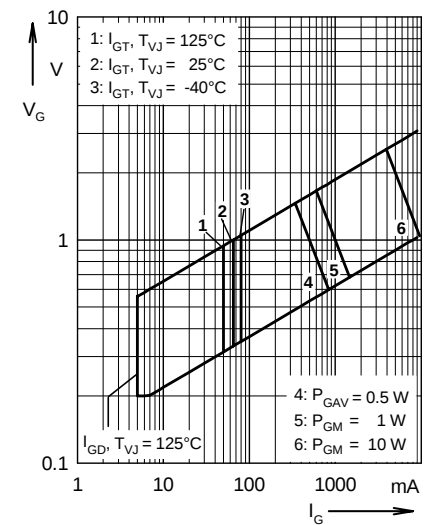
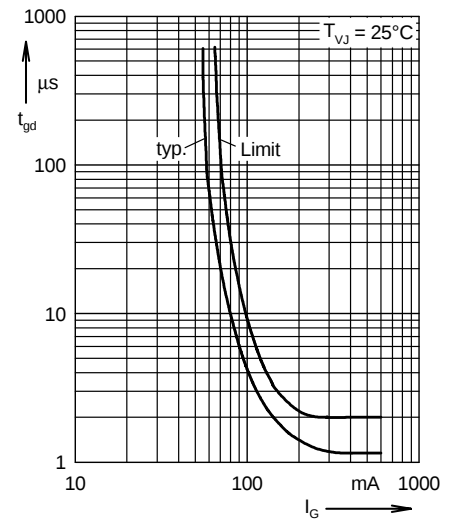


Fig. 1 Gate trigger range


Fig. 2 Gate controlled delay time t_{gd}

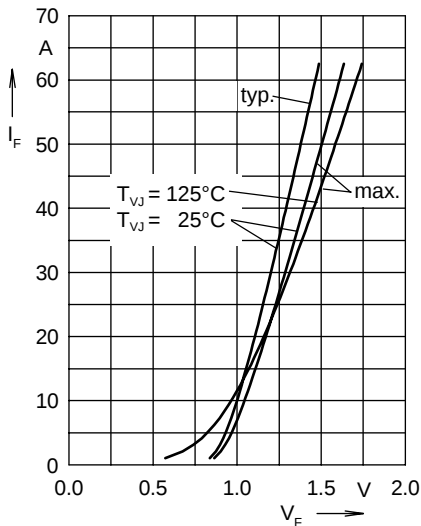


Fig. 3 Forward current versus voltage drop per diode

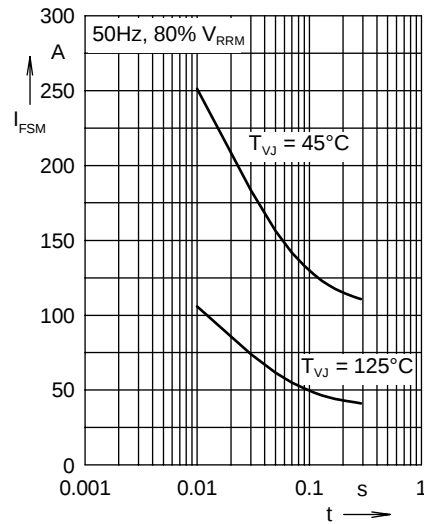


Fig. 4 Surge overload current

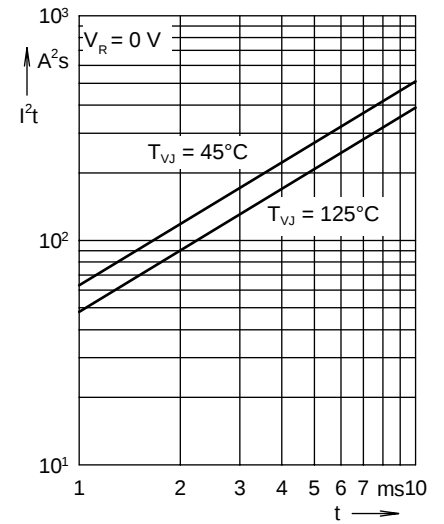


Fig. 5 I^2t versus time per diode

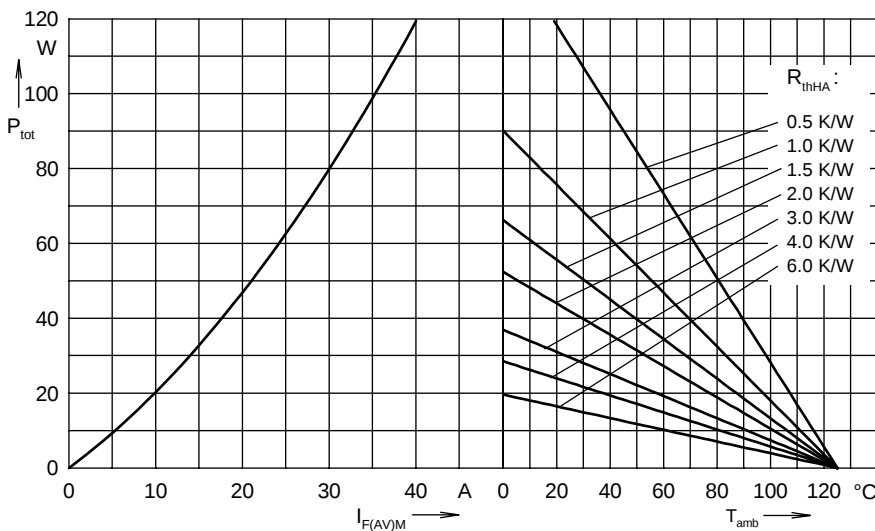


Fig. 6 Power dissipation versus direct output current and ambient temperature

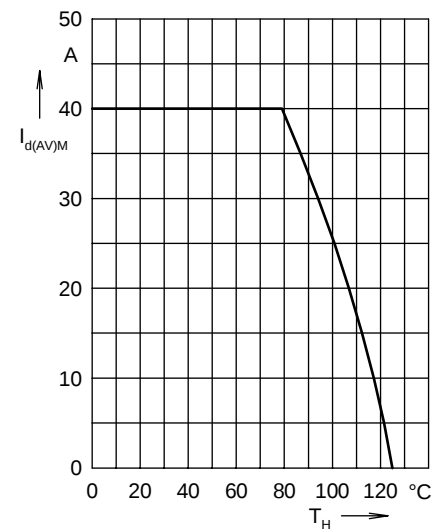


Fig. 7 Max. forward current versus heatsink temperature

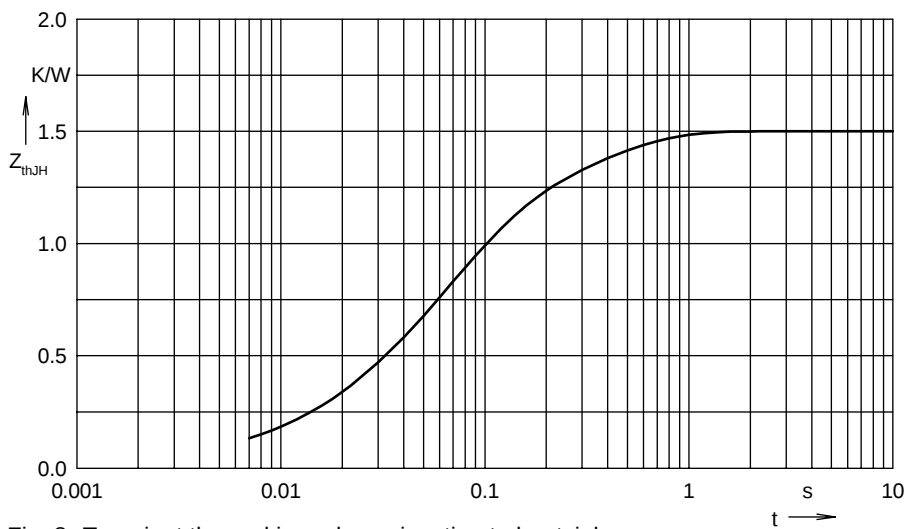


Fig. 8 Transient thermal impedance junction to heatsink

Constants for Z_{thJH} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.005	0.008
2	0.2	0.05
3	0.875	0.06
4	0.47	0.25